

Low temperature ALD of Ni from novel precursors

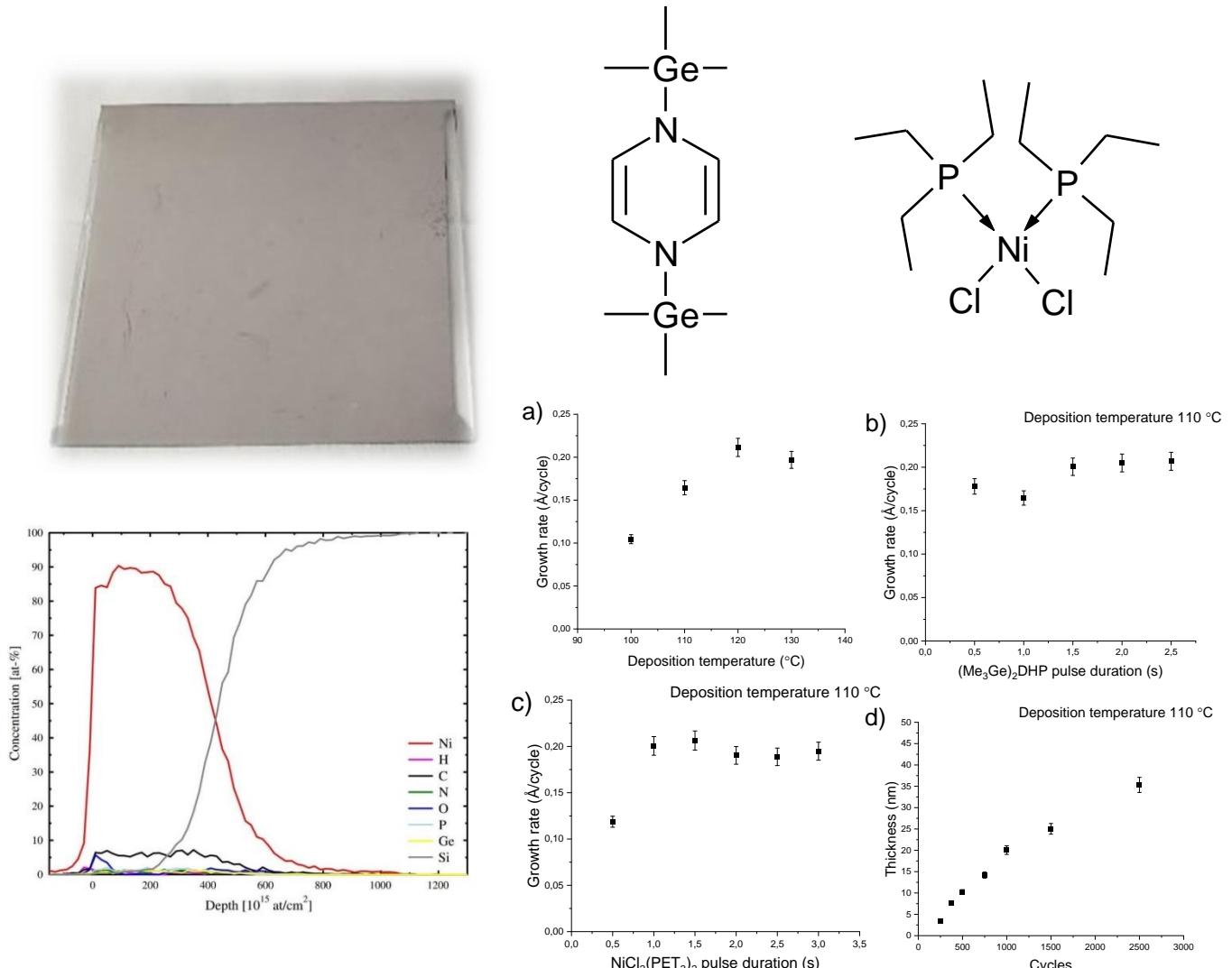


Figure 1. Top-left: 20 nm thick Ni film deposited on a soda lime glass substrate. Top-right-top: Structures of the precursors. Bottom-left: TOF-ERDA elemental depth profiles of a 35 nm thick Ni film. Bottom-right: Growth characteristics of the process. Growth rate as a function of a) deposition temperature, b) $(\text{Me}_3\text{Ge})_2\text{DHP}$ pulse length, and c) $\text{NiCl}_2(\text{PET}_3)_2$ pulse length. d) Film thickness as a function of deposition cycles.